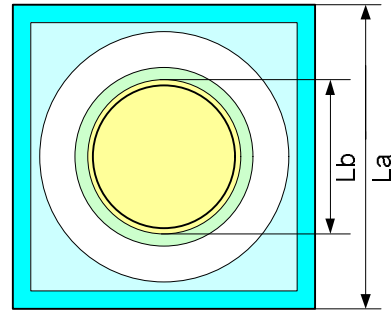


**2KG034350JL SWITCHING DIODE CHIPS**
**DESCRIPTION**

- 2KG034350JL is a high speed switching diode chip fabricated in planar technology.
- High reverse breakdown voltage rating.
- This chip can be encapsulated as MBD3004 switching diode.
- This chip has several thicknesses, can suit for different plastic package. The top electrodes material is Al, and the back-side electrodes material is Au.
- Chip size: 0.34 X 0.34 (mm<sup>2</sup>);
- Chip Thickness: 155±20μm or 180±20μm;


**2KG034350JL CHIP TOPOGRAPHY**

La: Chip Size: 340μm;

Lb: Pad Size: 180μm;

**MAXIMUM RATINGS (Ta=25°C)**

Characteristics	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	VRRM	350	V
DC Blocking Voltage	VR	300	V
Forward Continuous Current	IF	225	mA
Peak Forward Surge Current@1.0μs	IFSM	4.0	A
Maximum Operation Junction Temperature	TJ	150	°C
Storage Temperature Range	TSTG	-65~+150	°C

**ELECTRICAL CHARACTERISTICS (Ta=25°C)**

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Forward Voltage	VF	IF=20mA.	--	--	0.87	V
		IF=100mA.	--	--	1.0	V
		IF=200mA.	--	--	1.25	V
Reverse Voltage	VBR	IB=100μA.	350	--	--	V
Reverse Current	IR	VR=240V.	--	--	100	nA
Total Capacitance	CT	f=1MHz; VR=0.	--	--	5.0	pF
Reverse Recovery Time	Trr+	IF=IR=30mA, RL=100Ω; measured at IR=3mA.	--	--	50	ns